What is claimed is:

1. A method of fabricating a metal layer in an integrated circuit, the method comprising the steps of:

depositing a layer of metal alloy which contains alloy dopant precipitates;

performing a first anneal of the integrated circuit to drive the alloy dopants into solid solution;

quenching the integrated circuit to prevent the alloy dopants from coming out of solution;

removing excess metal alloy using a polish process;

performing a second anneal after the excess metal alloy is removed to allow the dopants to come out of solution and increase a conductivity of the metal alloy.

2. The method of claim 1 wherein the first anneal is performed at 400 to 500° C.

3. The method of claim 1 wherein the metal alloy comprises aluminum with alloy dopants of silicon and copper.

4. The method of claim 1 wherein the second anneal is performed at 150 to 250° C.

5. The method of claim 1 further comprising the steps of:

forming vias and interconnect trenches in the integrated circuit prior to depositing the layer of metal alloy; and

wherein the polish process removes excess metal alloy to define metal interconnect lines.

6. A method of fabricating a metal layer in an integrated circuit, the method comprising the steps of:

forming vias and interconnect trenches in the integrated circuit;

depositing a layer of metal alloy which contains alloy dopant precipitates on the integrated circuit to fill the vias and interconnect trenches;

performing a first anneal of the integrated circuit at 400 to 500° C to drive the alloy dopants into solid solution;

quenching the integrated circuit to prevent the alloy dopants from coming out of solution;

removing excess metal alloy using a chemical-mechanical polish process;

performing a second anneal at 150 to 250° C after the excess metal alloy is removed to allow the dopants to come out of solution and increase a conductivity of the metal alloy.

7. The method of claim 6 wherein the metal alloy comprises aluminum with alloy dopants of silicon and copper.

8. Method of improving a chemical-mechanical polish (CMP) process in an integrated circuit, the method comprises the step of annealing the integrated circuit prior to performing the chemical-mechanical polish process to drive alloy dopants into solid solution.

9. The method of claim 8 wherein the anneal is performed at approximately 400 to 500° C.

10. The method of claim 8 wherein the method further comprises annealing the integrated circuit after performing the chemical-mechanical polish process to drive alloy dopants out of solid solution.

11. The method of claim 10 wherein the anneal after chemical-mechanical polish is performed at approximately 100 to 250° C.

12. The method of claim 8 wherein the integrated circuit comprises an aluminum based alloy.

13. The method of claim 12 wherein the aluminum based alloy comprises Al, Cu and Si.

14. A method of polishing an aluminum based alloy in an integrated circuit, the method comprises the steps of:

annealing the integrated circuit at a temperature sufficient to drive alloy dopants into solid solution; and

performing a chemical mechanical polish on the integrated circuit to remove portions of the aluminum based alloy.

15. The method of claim 14 wherein the anneal is performed at approximately 400 to 500° C.

16. The method of claim 14 wherein the method further comprises annealing the integrated circuit after performing the chemical mechanical polish process at a temperature sufficient to drive alloy dopants out of solid solution.

17. The method of claim 16 wherein the anneal after chemical-mechanical polish is performed at approximately 100 to 250° C.

18. A memory device comprising:

an array of memory cells;

internal circuitry; and

metal contacts and interconnects coupled to the memory array and internal circuitry, wherein the metal contacts and interconnects are formed by annealing the memory at a temperature sufficient to drive alloy dopants into solid solution prior to polishing the memory device to remove portions of a metal layer and form the metal contacts and interconnects.

19. The memory device of claim 18 wherein the memory device is annealed following the polishing the memory device to increase a conductivity of the metal contacts and interconnects.